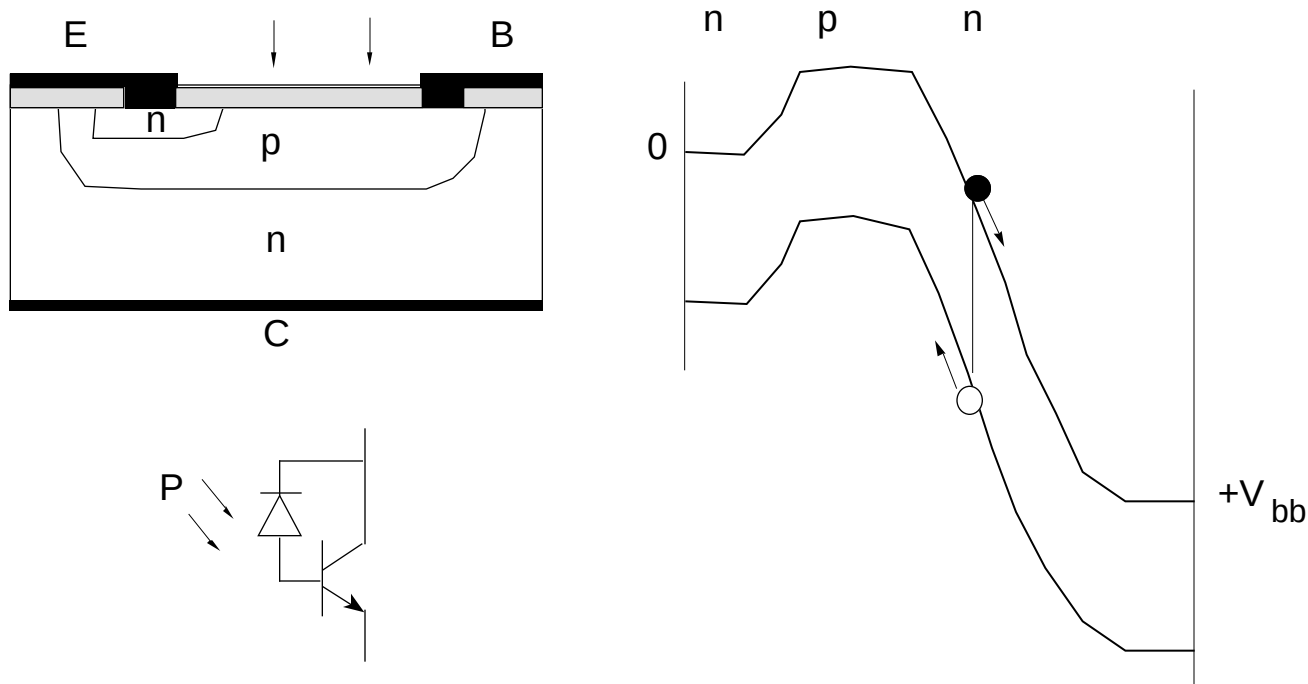
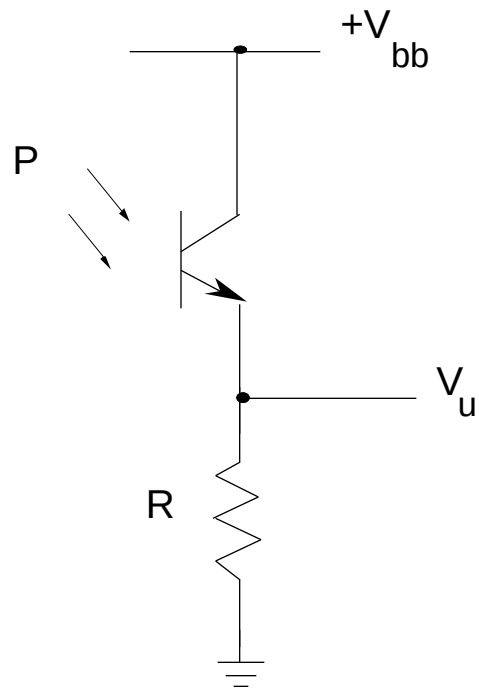


Bipolar Phototransistor



Bipolar transistor has a wide C-B junction adequate for photon dissipation, and an internal current amplification mechanism

Basic Scheme



$$I_C = (h_{fe} + 1)I_{ph} + I_{CE0} + h_{fe}I_B$$

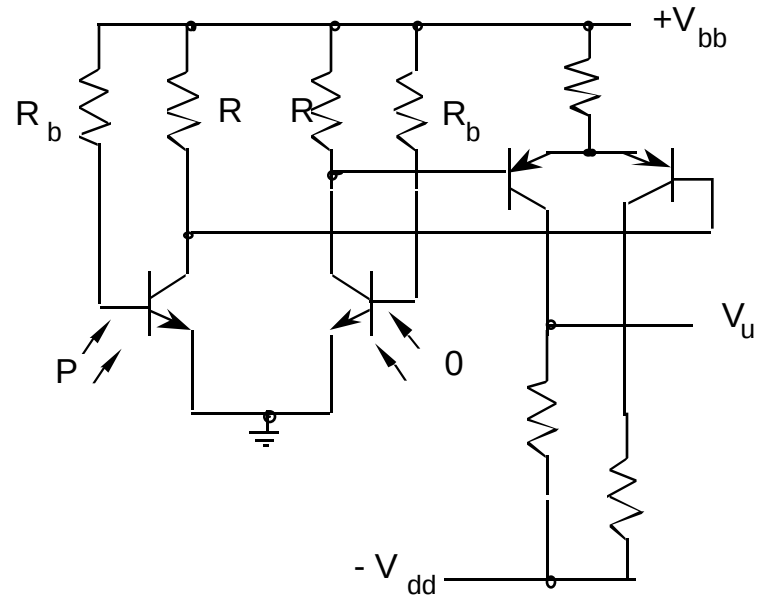
$$V_u = R [(h_{fe} + 1) \sigma P + I_{CE0}]$$

$$f_{hfe} = f_T / h_{fe}$$

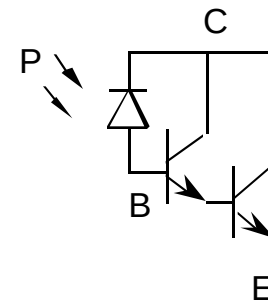
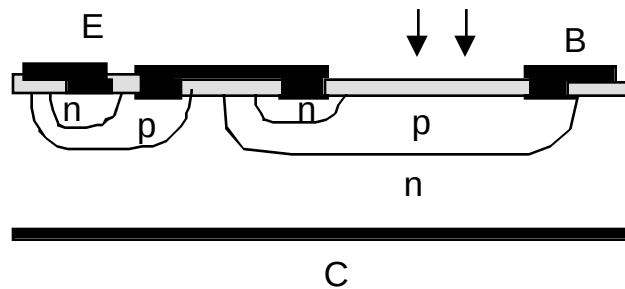
$$v_u^2 = 2eB(h_{fe} + 1)^2(\sigma P + I_{CB0})R^2 + 4kTBR$$

Differential scheme and photo-Darlington

Differential scheme
for base current
cancellation



Darlington
phototransistor



Avalanche Phototransistor

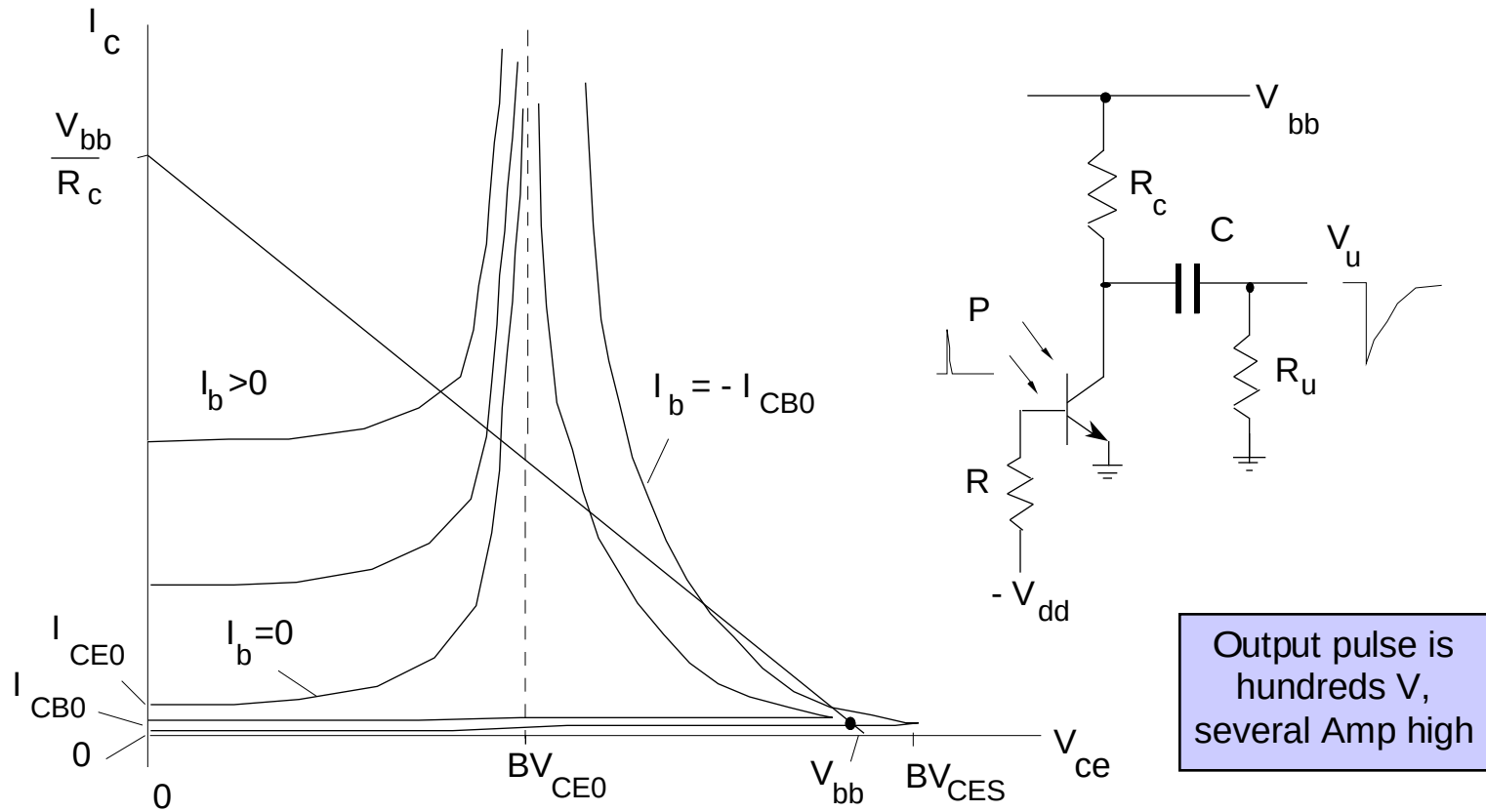
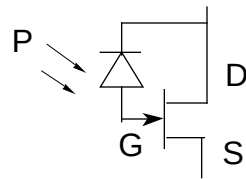
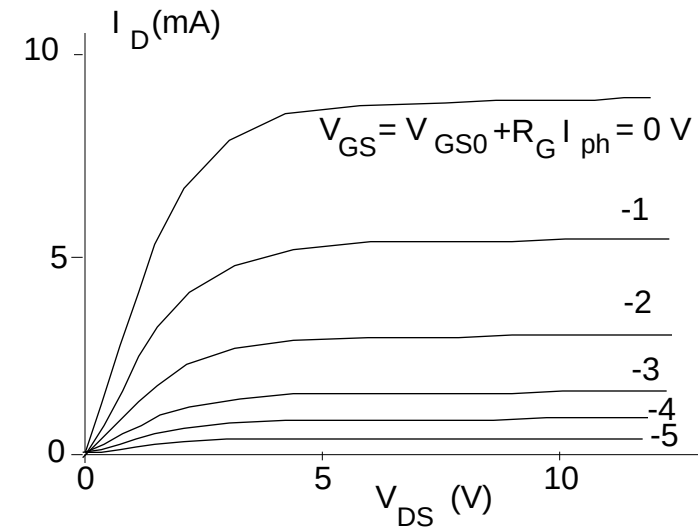
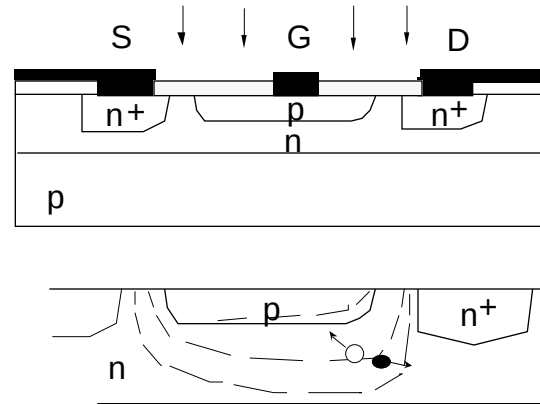


Photo J-FET



$$A_I = G_m R_G$$

$$f_2 = 1/2\pi R_G C_p$$

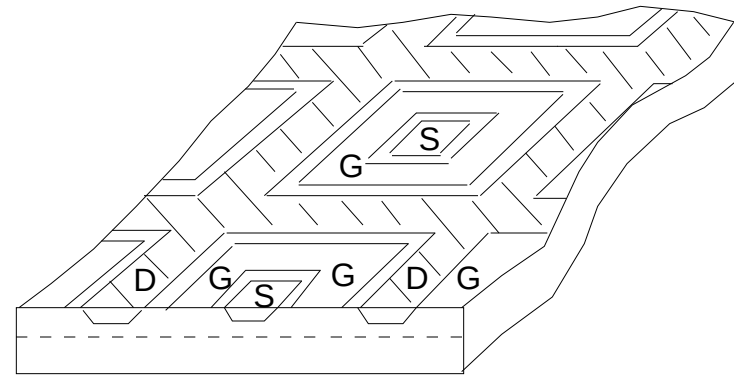
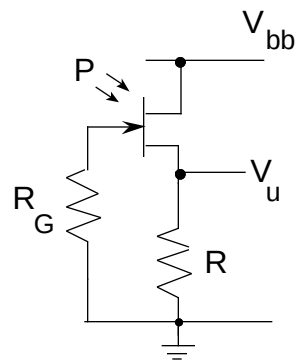


Photo-MOS

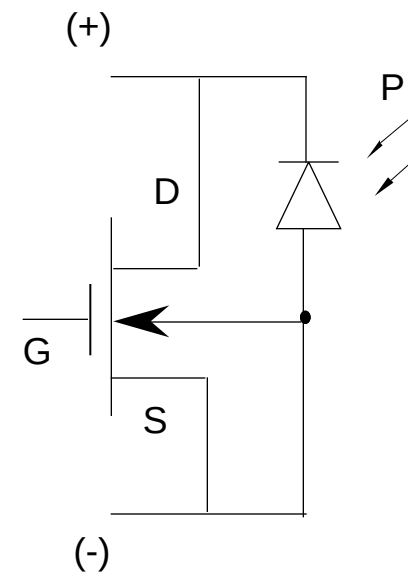
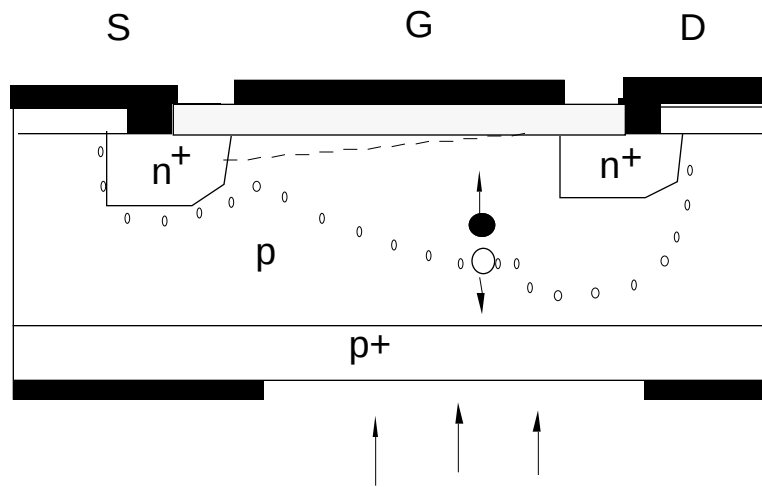
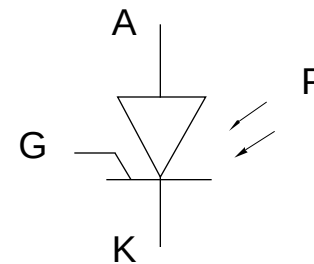
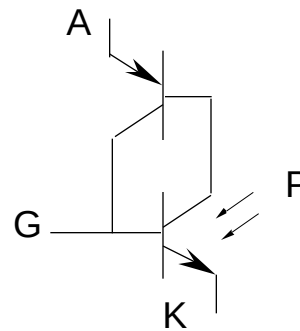
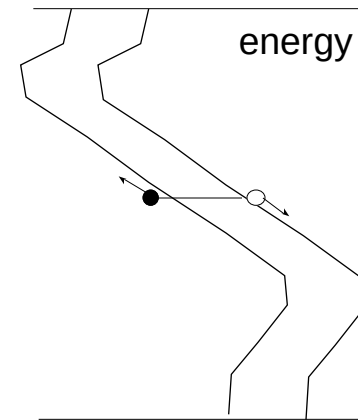
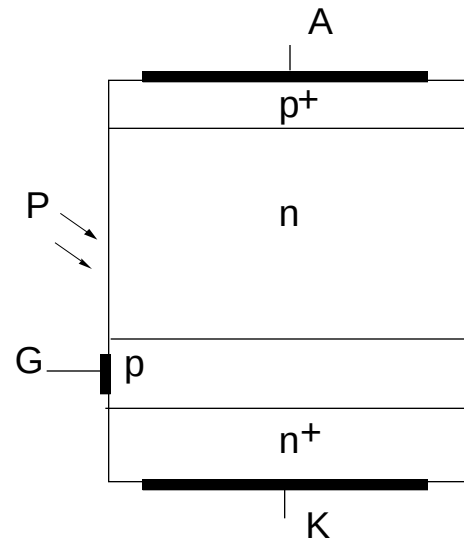


Photo -LASCR



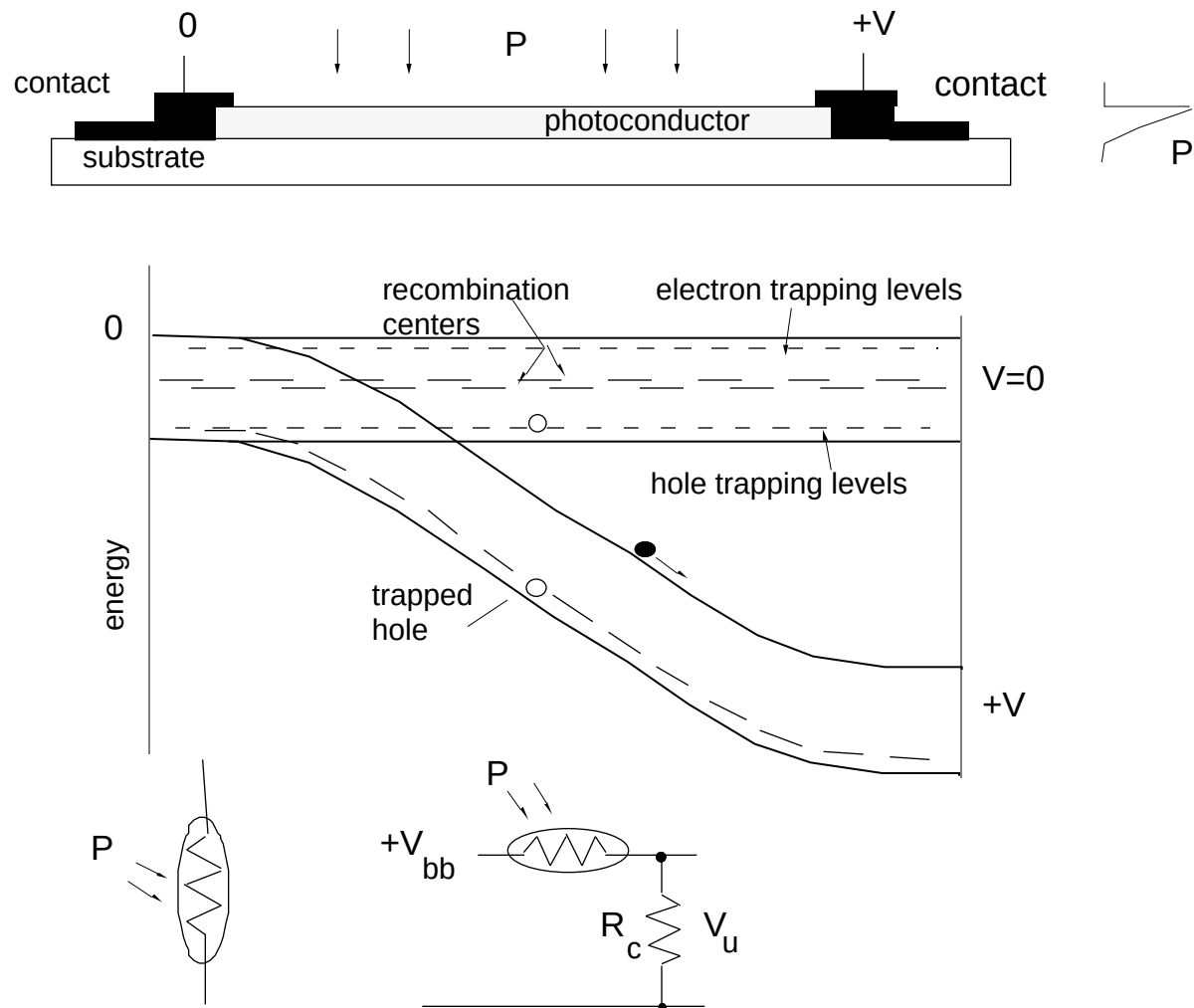
General

- photoconductivity was the **first photoelectric** effect being observed (in selenium, by W. Smith, **1873**)
- only requires a polycrystalline or amorphous semiconductor, deposited by evaporation or sputtering
- has **low cost** and on very **large areas**
- response covers **UV through FIR** spectral ranges
- has **internal gain**, though at expense of **bandwidth**
- leads **development** of other photodetectors in new materials/ spectral ranges

Fields of application

- single-element detectors for **industrial controls** (item counters, presence/proximity sensors, flame detectors, etc.);
- photometric devices for **exposure meters** and **luxmeters**;
- **thermal IR detectors** for detection, sensing, and non-contact thermometry;
- photosensitive layers (or **targets**) of vidicons and other image-pickup tubes;
- **photosensitive elements** of reprographic apparatus (photocopiers, laser printers) for transfer of toner to the paper copy

Principles



Gain and frequency response

gain: $M = 1 + \tau_{n,p}/T$

drift time: $T = L/v_{n,p} = L/\mu_{n,p}E = L^2/\mu_{n,p}V$

$$M = 1 + \tau_{n,p} \mu_{n,p} V/L^2$$

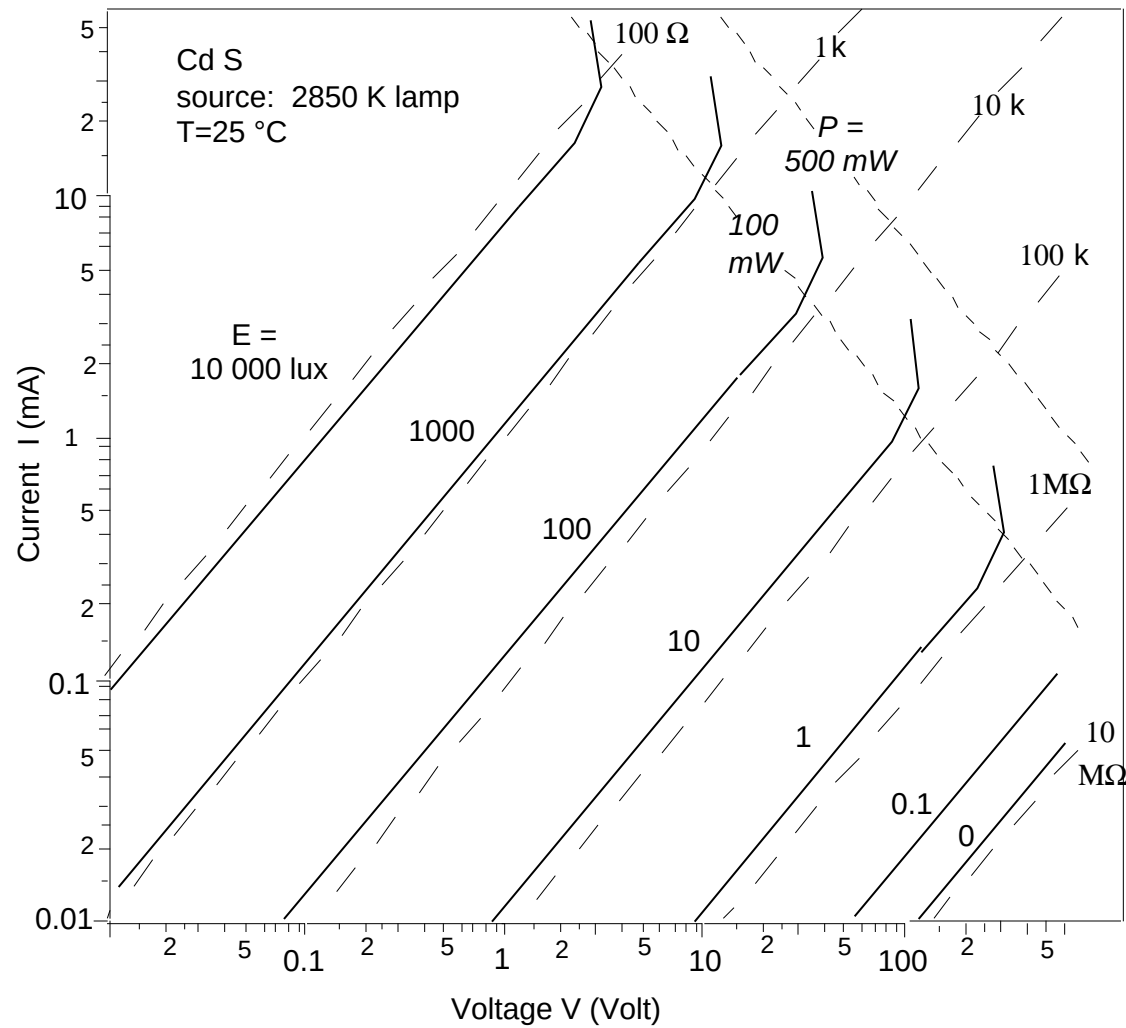
$$f_2 = 1/2\pi \tau_{n,p} \text{ so that } f_2 M \approx 1/2\pi T \approx \text{const}$$

conductance:

$$G = (I_b + MI_{ph})/V = G_b + M\sigma P/V = G_b + (1 + \tau_{n,p} \mu_{n,p} V/L^2)\sigma P/V$$

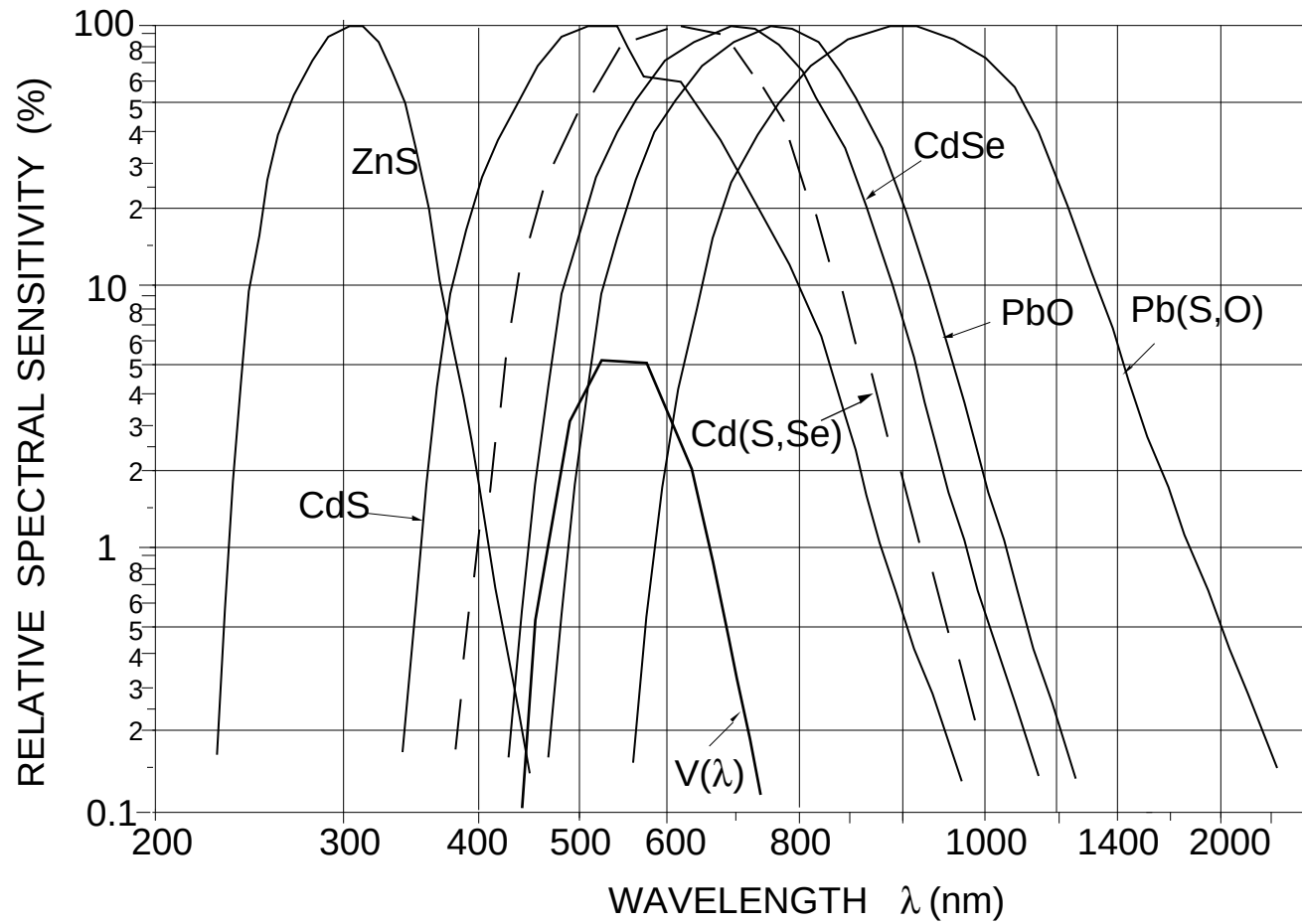
$$\text{or } G \approx G_b + (\sigma \tau_{n,p} \mu_{n,p} /L^2)P = G_b + \kappa P$$

Photoconductance characteristics



from: "Photodetectors", by S. Donati, Prentice Hall 2000

Spectral responses



from: "Photodetectors", by S. Donati, Prentice Hall 2000

Cryostat for IR detectors

